

SWITCHING N-CHANNEL POWER MOS FET

DESCRIPTION

NEC

The 2SK3484 is N-channel MOS Field Effect Transistor designed for high current switching applications.

FEATURES

- Low on-state resistance $R_{DS(on)1} = 125 \text{ m}\Omega \text{ MAX}. (V_{GS} = 10 \text{ V}, \text{ ID} = 8 \text{ A})$
- $R_{DS(on)2}$ = 148 m Ω MAX. (V_{GS} = 4.5 V, I_D = 8 A)
- Low Ciss: Ciss = 900 pF TYP.
- Built-in gate protection diode
- TO-251/TO-252 package

ABSOLUTE MAXIMUM RATINGS (TA = 25°C)

Drain to Source Voltage (V _{GS} = 0 V)	VDSS	100	V
Gate to Source Voltage (VDS = 0 V)	Vgss	±20	V
Drain Current (DC) (Tc = 25°C)	D(DC)	±16	Α
Drain Current (pulse) Note1	D(pulse)	±22	Α
Total Power Dissipation (Tc = 25°C)	P T1	30	W
Total Power Dissipation ($T_A = 25^{\circ}C$)	Pt2	1.0	W
Channel Temperature	Tch	150	°C
Storage Temperature	Tstg	–55 to +150	°C
Single Avalanche Current Note2	las	10	Α
Single Avalanche Energy Note2	Eas	10	mJ

★ ORDERING INFORMATION

PART NUMBER	PACKAGE		
2SK3484	TO-251 (MP-3)		
2SK3484-Z	TO-252 (MP-3Z)		

(TO-251)



(TO-252)



Notes 1. PW \leq 10 μ s, Duty Cycle \leq 1%

2. Starting T_{ch} = 25°C, V_{DD} = 50 V, R_G = 25 Ω , V_{GS} = 20 \rightarrow 0 V

THERMAL RESISTANCE

Channel to Case Thermal Resistance	Rth(ch-C)	4.17	°C/W
Channel to Ambient Thermal Resistance	Rth(ch-A)	125	°C/W

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The mark \star shows major revised points.

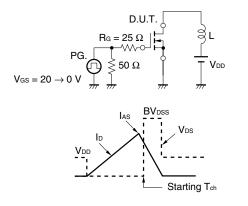
ELECTRICAL CHARACTERISTICS (TA = 25°C)

CHARACTERISTICS	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Zero Gate Voltage Drain Current	loss	V _{DS} = 100 V, V _{GS} = 0 V			10	μA
Gate Leakage Current	lgss	V _{GS} = ±20 V, V _{DS} = 0 V			±10	μA
Gate Cut-off Voltage	V _{GS(off)}	V _{DS} = 10 V, I _D = 1 mA	1.5	2.0	2.5	V
Forward Transfer Admittance Note	y _{fs}	V _{DS} = 10 V, I _D = 8 A	4.7	9.5		S
Drain to Source On-state Resistance Note	RDS(on)1	V _{GS} = 10 V, I _D = 8 A		100	125	mΩ
	RDS(on)2	V _{GS} = 4.5 V, I _D = 8 A		110	148	mΩ
Input Capacitance	Ciss	V _{DS} = 10 V		900		pF
Output Capacitance	Coss	V _{GS} = 0 V		110		pF
Reverse Transfer Capacitance	Crss	f = 1 MHz		50		pF
Turn-on Delay Time	td(on)	V _{DD} = 50 V, I _D = 8 A		9.0		ns
Rise Time	tr	V _{GS} = 10 V		5.0		ns
Turn-off Delay Time	td(off)	R _G = 0 Ω		30		ns
Fall Time	tr			4.0		ns
Total Gate Charge	QG	V _{DD} = 80 V		20		nC
Gate to Source Charge	Q _{GS}	V _{GS} = 10 V		3.0		nC
Gate to Drain Charge	QGD	ID = 16 A		5.0		nC
Body Diode Forward Voltage Note	VF(S-D)	IF = 16 A, VGS = 0 V		1.0		V
Reverse Recovery Time	trr	I⊧ = 16 A, V₀s = 0 V		60		ns
Reverse Recovery Charge	Qrr	di/dt = 100 A/ μs		122		nC

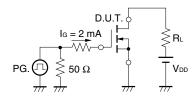
Note Pulsed

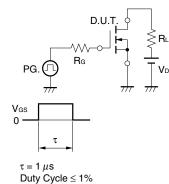
TEST CIRCUIT 1 AVALANCHE CAPABILITY

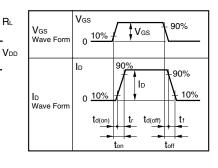
TEST CIRCUIT 2 SWITCHING TIME



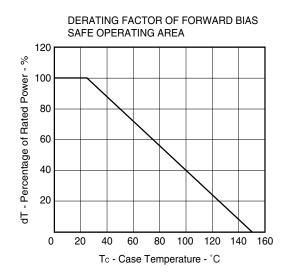
TEST CIRCUIT 3 GATE CHARGE



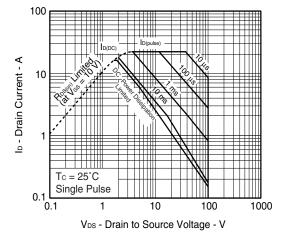


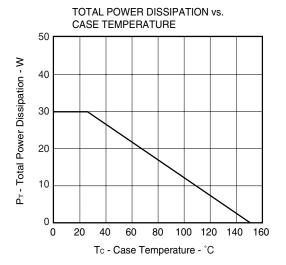


TYPICAL CHARACTERISTICS ($T_A = 25^{\circ}C$)

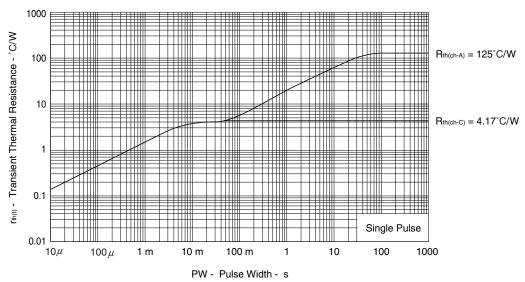






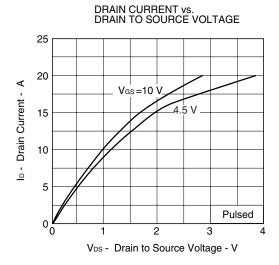


TRANSIENT THERMAL RESISTANCE vs. PULSE WIDTH

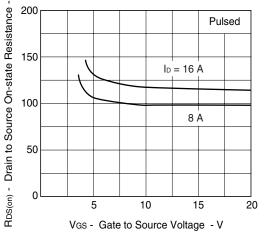


100 Pulsed $V_{DS} = 10 V$ Ip - Drain Current - A 10 $T_A = -40^{\circ}C$ 1 25°C 75°C 150°C 0.1 0.01 5 2 3 4 1 VGS - Gate to Source Voltage - V

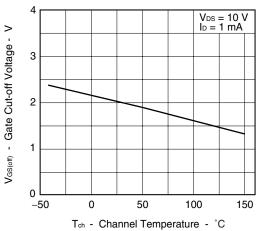
FORWARD TRANSFER CHARACTERISTICS



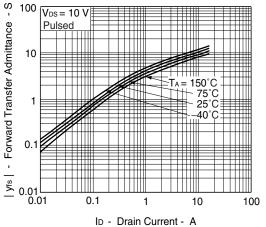
DRAIN TO SOURCE ON-STATE RESISTANCE vs. GATE TO SOURCE VOLTAGE ст Сш

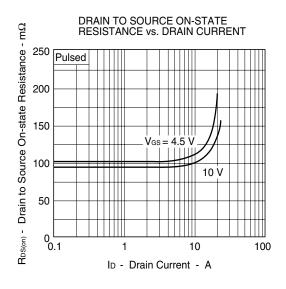


GATE CUT-OFF VOLTAGE vs. CHANNEL TEMPERATURE

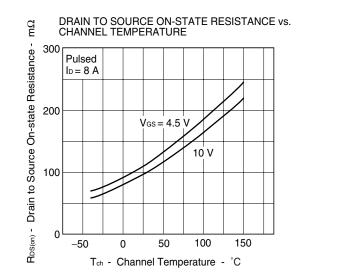


FORWARD TRANSFER ADMITTANCE vs. DRAIN CURRENT 100 $V_{DS} = 10 V$ Pulsed

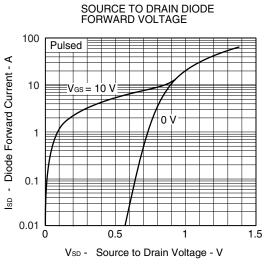




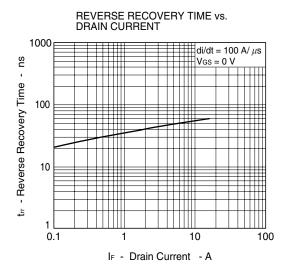
Data Sheet D15069EJ2V0DS



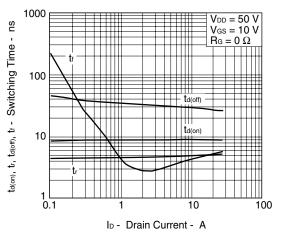
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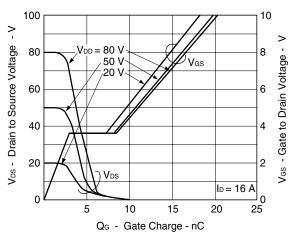
CAPACITANCE vs. DRAIN TO SOURCE VOLTAGE 10000 V_{GS} = 0 V f = 1 MHz ₩ Ciss, Coss, Crss - Capacitance - pF C 1000 100 Crss 10 0.01 0.1 1 10 100 VDS - Drain to Source Voltage - V

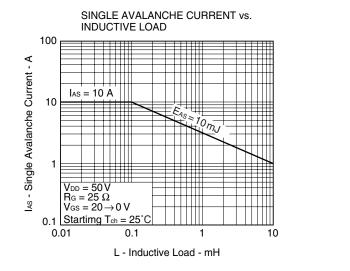


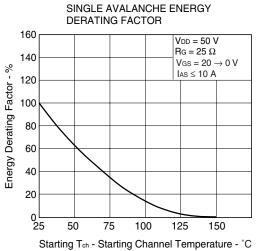
SWITCHING CHARACTERISTICS



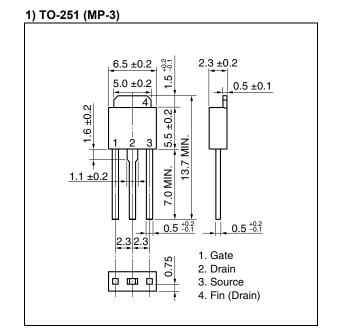
DYNAMIC INPUT/OUTPUT CHARACTERISTICS

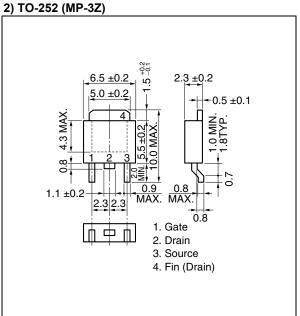




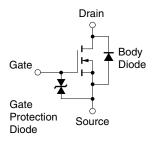


★ PACKAGE DRAWINGS (Unit: mm)





EQUIVALENT CIRCUIT



Remark The diode connected between the gate and source of the transistor serves as a protector against ESD. When this device actually used, an additional protection circuit is externally required if a voltage exceeding the rated voltage may be applied to this device.

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